Abstracts

A 3 V, 0.35 /spl mu/m CMOS Bluetooth receiver IC

Wenjun Sheng, Bo Xia, A. Emira, Chunyu Xin, A.Y. Valero-Lopez, Sung Tae Moon and E. Sanchez-Sinencio. "A 3 V, 0.35 /spl mu/m CMOS Bluetooth receiver IC." 2002 Radio Frequency Integrated Circuits (RFIC) Symposium 02. (2002 [RFIC]): 107-110.

This paper presents a monolithic low-IF Bluetooth receiver. The highlights of the receiver include a low-power active complex filter with a non-conventional tuning scheme and a high performance mixed-mode GFSK demodulator. The chip was fabricated on a 6.25 mm/sup 2/ die using TSMC 0.35 /spl mu/m standard CMOS process. -82 dBm sensitivity at 1e-3 BER, -10 dBm IIP3 and 15 dB noise figure were achieved In the measurements.

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